Very Low Forward Voltage Trench-based Schottky Rectifier

Features

- Fine Lithography Trench–based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb–Free Devices

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR–ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

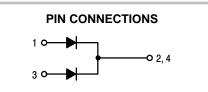
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

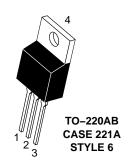


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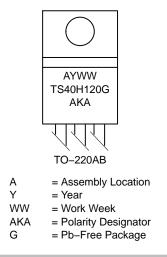
http://onsemi.com

VERY LOW FORWARD VOLT-AGE, SCHOTTKY BARRIER RECTIFIERS 40 AMPERES, 120 VOLTS





MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	120	V
Average Rectified Forward Current (Rated V_R , $T_C = 124^{\circ}C$) (Rated V_R , $T_C = 132^{\circ}C$)	Per device Per diode	I _{F(AV)}	40 20	A
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, $T_C = 119^{\circ}C$) (Rated V _R , Square Wave, 20 kHz, $T_C = 130^{\circ}C$)	Per device Per diode	I _{FRM}	80 40	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	250	A
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T _{stg}	-40 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rat	ng	Symbol	NTST40H120CTG	Unit
Maximum Thermal Resistance per Device	Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	0.81 70	°C/W °C/W

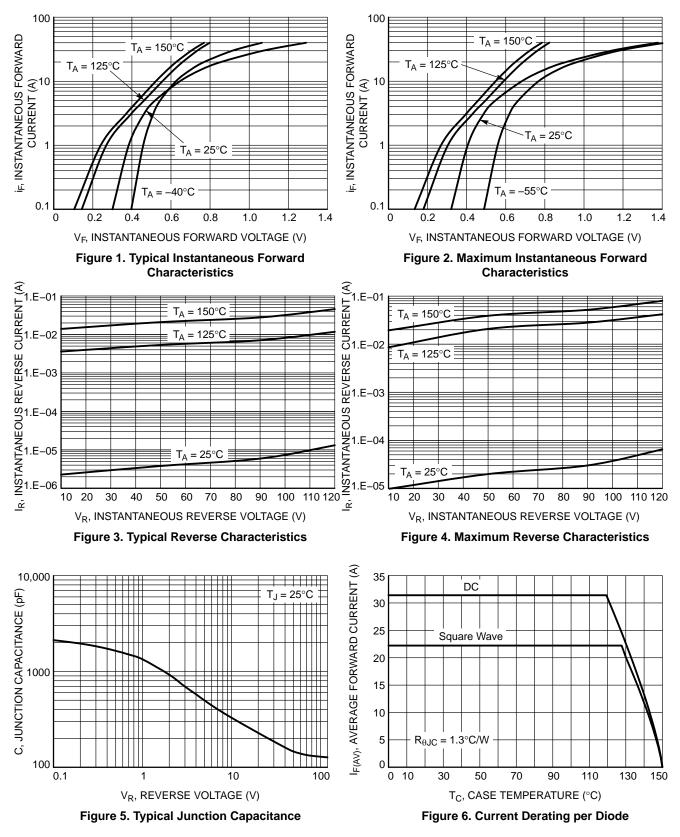
ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
$\label{eq:maximum lnstantaneous Forward Voltage (Note 1)} \begin{array}{l} (I_F=5 \ A, \ T_J=25^\circ C) \\ (I_F=10 \ A, \ T_J=25^\circ C) \\ (I_F=20 \ A, \ T_J=25^\circ C) \end{array}$	VF	0.52 0.65 0.85	_ 	V
$(I_{F} = 5 \text{ A}, T_{J} = 125^{\circ}\text{C})$ $(I_{F} = 10 \text{ A}, T_{J} = 125^{\circ}\text{C})$ $(I_{F} = 20 \text{ A}, T_{J} = 125^{\circ}\text{C})$		0.46 0.55 0.66	_ _ 0.69	
Maximum Instantaneous Reverse Current (Note 1) $(V_R = 90 \text{ V}, T_J = 25^{\circ}\text{C})$ $(V_R = 90 \text{ V}, T_J = 125^{\circ}\text{C})$	۱ _R	6 7		μA mA
(Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 125^{\circ}C$)		_ 20	65 42	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle $\leq 2.0\%$

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

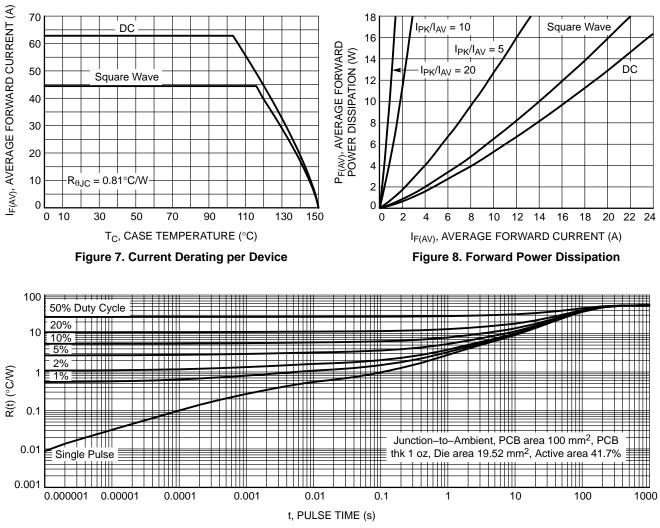


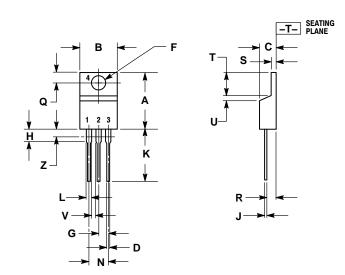
Figure 9. Thermal Characteristics

ORDERING INFORMATION

Device	Package	Shipping
NTST40H120CTG	TO-220AB (Pb-Free)	50 Units / Rail

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AF**



NOTES

DIMENSIONING AND TOLERANCING PER ANSI 1.

214.5M, 1982. CONTROLLING DIMENSION: INCH. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE 2. 3. ALLOWED.

	INCHES		INCHES MILLIMETER	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
Κ	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Ζ		0.080		2.04

PIN 1. ANODE CATHODE 2. 3. ANODE 4 CATHODE

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